

Customer No.: 31561
Application No: 10/707,358
Docket No.:11417-US-PA

Claim Amendment

Please amend the claims according to the following listing of claims and substitute it for all prior versions and listings of claims in the application.

In The Claims

Claims 1-19 (canceled).

20. (currently amended) A semiconductor device structure, the structure comprising:
~~a gate dielectric layer, an active region and an isolation region, disposed on a substrate;~~
~~a plurality of first gate structures having a gate conductive layer, disposed on the gate dielectric layer substrate, wherein first portions of the first-gate structures, disposed on the active region, further comprise a cap layer and a spacer, and second portions of the gate structures, disposed on the isolation region, do not comprise a gate conductive layer, a cap layer and a spacer;~~
~~a plurality of second gate structures, disposed on the substrate, wherein the second gate structures comprise the gate conductive layer;~~
~~a dielectric layer, disposed on above the substrate, covering the first and the second gate structures;~~
~~a self-aligned contact, disposed in the dielectric layer between the first two of the first portions of the gate structures; and~~

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a conductive line, disposed on the dielectric layer, wherein the conductive line electrically connects with the self-aligned contact.

21. (currently amended) The structure of claim 20, wherein the cap layer and the spacer of the first portions of the first gate structures are is disposed between the self-aligned contact and the gate conductive layer and a part of the cap layer, abutted to the spacer disposed between the self-aligned contact and the gate conductive layer, remains on the first portions of the gate structures.

22. (withdrawn) The structure of claim 20, wherein the dielectric layer at a sidewall of the gate conductive layer of the second gate structures comprises voids therein.

23. (withdrawn) The structure of claim 22, wherein the dielectric layer at a sidewall of the gate conductive layer of the first gate structures that is not adjacent to the self-aligned contact comprises voids therein.

24. (withdrawn) The structure of claim 20, wherein the second gate structures further comprise a spacer, disposed on a sidewall of the second gate structures, wherein the spacer is higher than the gate conductive layer.

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25. (original) The structure of claim 20, wherein a dielectric constant of the dielectric layer is lower than a dielectric constant of the cap layer and the spacer.

26. (currently amended) The structure of claim 20 further comprising a metal silicide layer formed on a sidewall of the gate conductive layer of the second portions of the gate structures.

27. (withdrawn) The structure of claim 26, wherein a sidewall of the gate conductive layer of the first gate structures that is not adjacent to the self-aligned contact further comprises the metal silicide layer.

Claims 28-31 (canceled).